

Product Overview

NTHS4101P: Single P-Channel ChipFET™ Power MOSFET -20V -6.7A 34mΩ

For complete documentation, see the data sheet.

Power MOSFET -20 V, -6.7 A, Single P-Channel ChipFET™

Features

- Offers an Ultra Low RDS(on) Solution in the ChipFet™ Package
- Miniature ChipFet™ Package with 40 % Smaller Footprint than TSOP-6, makes it an ideal device for Applications where board space is at a premium.
- Low Profile (< 1.1 mm) allows it to fit easily into extremely thin environments such as Portable Electronics.
- Designed to Provide Low RDS(on) at Gate Voltage (as low as 1.8V). The Operating Voltage used in many Logic ICs in Portable Electronics.
- Simplifies Circuit Design since Additional Boost Circuits for Gate Voltages are not required.
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migrations to Lower Levels using the same Basic Topology.

Applications

- Optimized for Battery and Load Management Applications in Portable Equipment and other Portable Applications
- Charge Control in Battery Chargers
- Buck and Boost Converters

End Products

- MP3 Players
- Cell Phones
- Digital Cameras
- PDAs

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DSS} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
NTHS4101PT1G	0.3011	Pb-free Halide free	Active	P-Channel	Single	-20	8	1.5	4.8	1.3	30	21	-	-	25	2100	Chip FET-8

For more information please contact your local sales support at www.onsemi.com.

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